



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Application of :  
Hirofumi HARADA :  
Serial No. 09/872,798 : Group Art Unit: 2814  
Filed: June 1, 2001 : Examiner: Thao X. Le  
For: VERTICAL MOS TRANSISTOR :  
AND A METHOD OF :  
MANUFACTURING THE SAME : Docket No. S004-4310(RCE)

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COMMISSIONER OF PATENTS AND TRADEMARKS  
Washington, DC 20231

AMENDMENT UNDER 37 CFR §1.114

S I R:

In response to the final Office Action dated  
November 29, 2002, applicant amends his application as  
follows:

IN THE SPECIFICATION:

Replace the paragraph beginning 4 lines from the  
bottom of page 8 with the following rewritten paragraph:

--Fig. 1 is a sectional view of an N channel  
vertical MOS transistor according to the present invention. A